



Global Communication Semiconductors, LLC

Corporate & Foundry
23155 Kashiwa Court, Torrance, CA. 90505
Telephone: 310-530-7274 Fax: 310-517-8200
Website: www.gcsincorp.com

Sr. GaN HEMT Device / Integration Engineer

Job Req. #0636
Department: RF and Power Technology
Status: Full-Time/ Exempt
Shift: Day

Job Description

- Lead GaN HEMT device/process development and yield improvement efforts, including 0.5um, 0.25um, and 0.15um GaN HEMT processes.
- Perform device fabrication, characterization, and qualification.
- Support trouble-shooting, failure analysis, and yield improvement in related production processes.
- Interact with customers and manufacturing staff.
- Manage R&D projects.

Job Requirements

- Ph.D. or Master's degree in EE, Physics, or Material Science
- 5+ years of industrial experience in semiconductor wafer fab environment
- 3+ years of direct hands-on experience in GaN HEMT technology.